

In situ observation of chemical reaction inside a micro reaction capsule in SEM/DualBeam

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Application and Product Specialist EMEA



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4/26/2021
2:56:02 PM

HV
10.00 kV

curr
0.40 nA

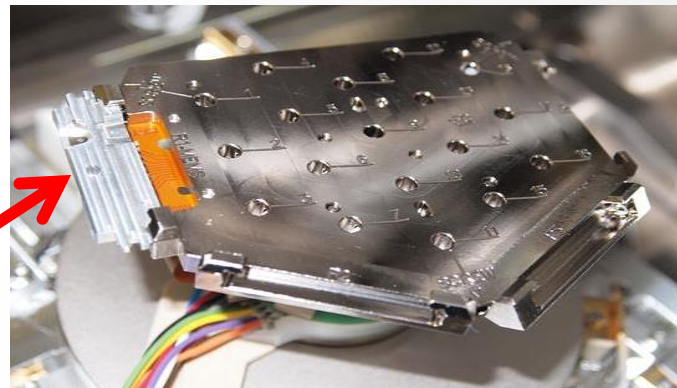
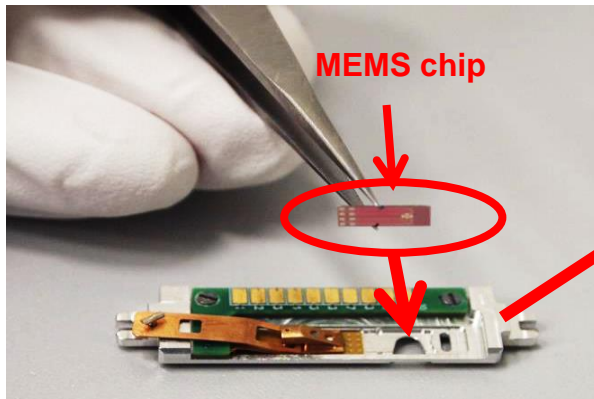
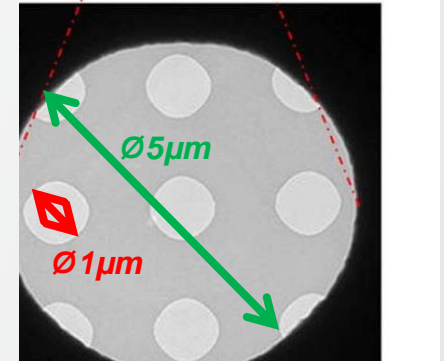
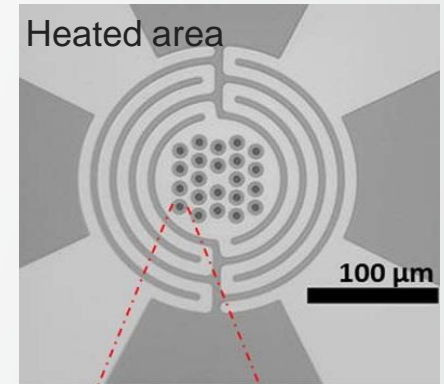
det
TLD

mo
SE



μHeater – MEMS based heating device

- Microheating device based on MEMS technology-solution for **TEM** & **SEM/DualBeam**, under **high vacuum**
- Compatible with all types of detectors: **SE, BSE, STEM, EDS, EBSD**
- Temperature up to **1200°C**
- Maximum ramping speed: **up to 10^4 °C/s**
 - Software allows any slower rate
- No compromise in the SEM resolution
- No stage limits (incl. full rotation)
- Support sample size: **nm ~ hundred μm**



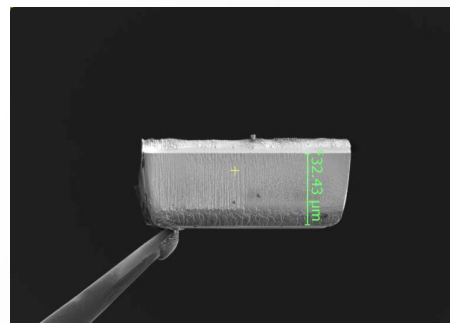
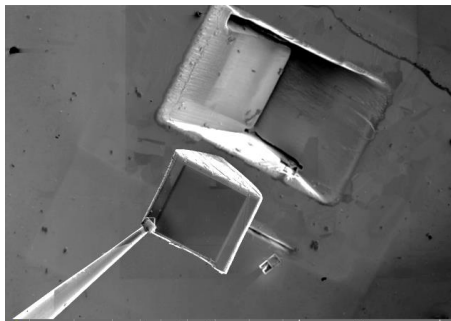
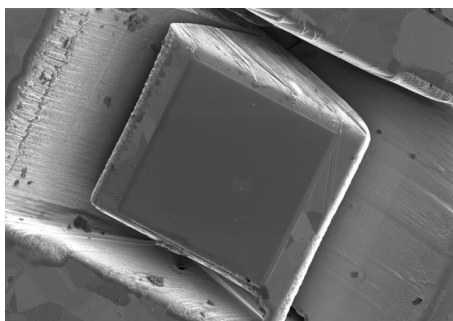
Multipurpose holder with slot for μHeater cartridge

Ref: DOI: 10.1002/jemt.22623

μHeater sample preparation

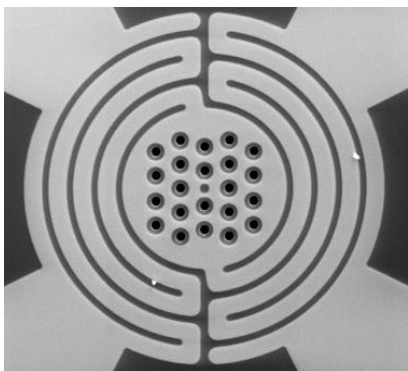
A: Chunk fabrication using FIB

1. Chunk fabricated from bulk
2. FIB lift out
3. On-needle cleaning
4. Chunk on MEMS heater

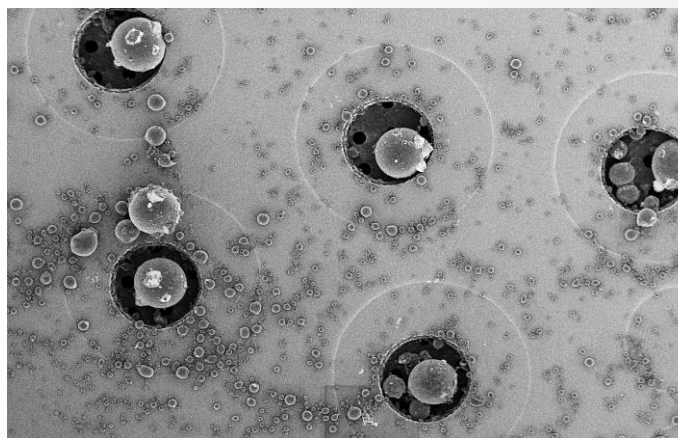


80μm x 35μm Ni superalloy chunk on MEMS chip.

B: Nanoparticles, powders

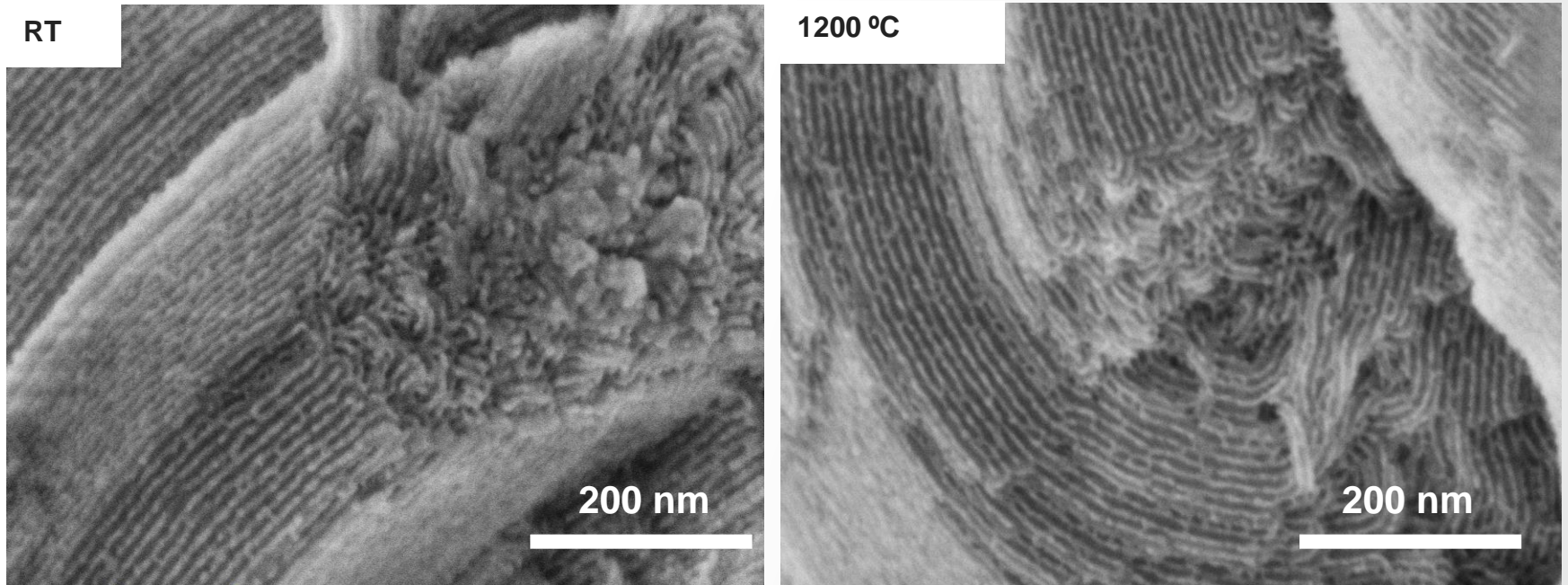


Mesoporous silica SBA-15



Sn nanoparticles on MEMS chip. The HFW is 41.2μm.

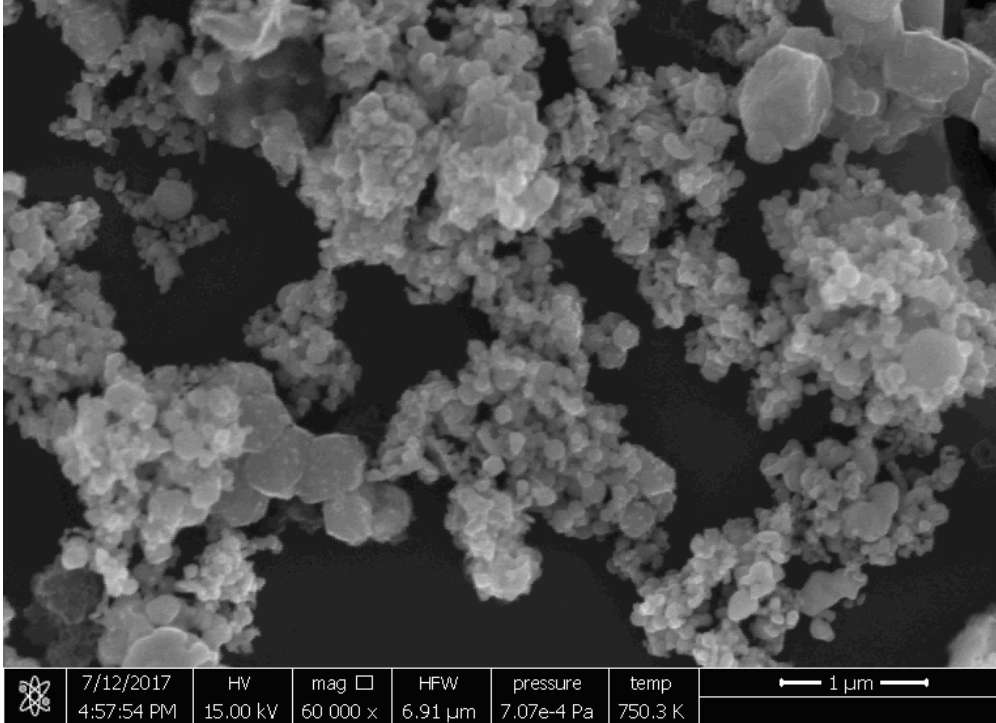
High resolution during heating on μ Heater



The HFW is 690 nm.

SBA15 nanoparticles on μ Heater. The nanoparticles were heated from room temperature to 1200°C at a heating rate of 1000°C/s. SE image was taken at room temperature and at 1200°C. It shows high resolution images can be taken even at 1200°C on μ Heater.

μ Heater – 1200° C heating with millisecond temperature control



Mix of Sn, Cu, Ag nanoparticles heated from 477° to 1200° C in real time
Image courtesy: Min Wu, Thermo Fisher Brno

μ Heater:

- Ramp up to 1200° C in 100 ms
- 100 μm sample size

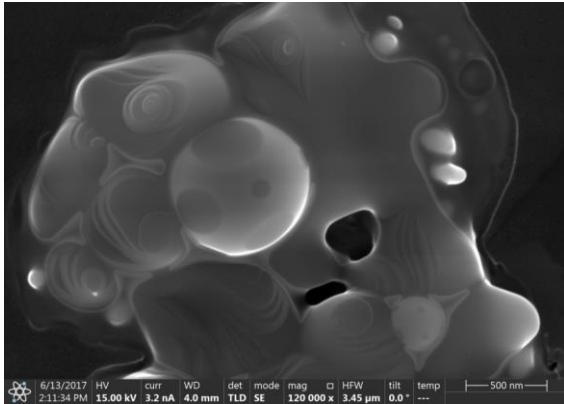
Benefits:

- Observation of rapid heating effects
- Work at high magnification
- Enables practical nanoparticle heating experiments

μ Heater: Extreme ramp rate, stability and image quality

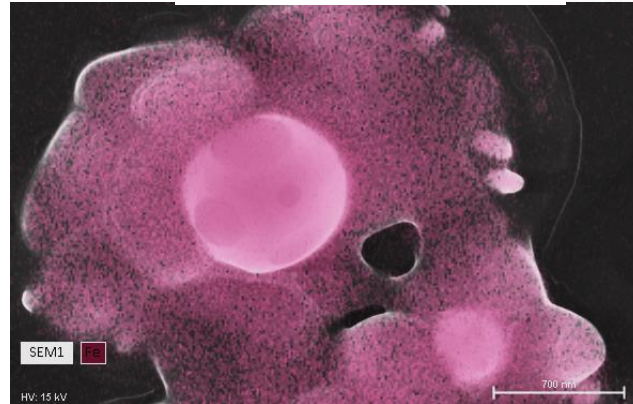
μHeater enables in situ EDS at Elevated Temperature

1050° C

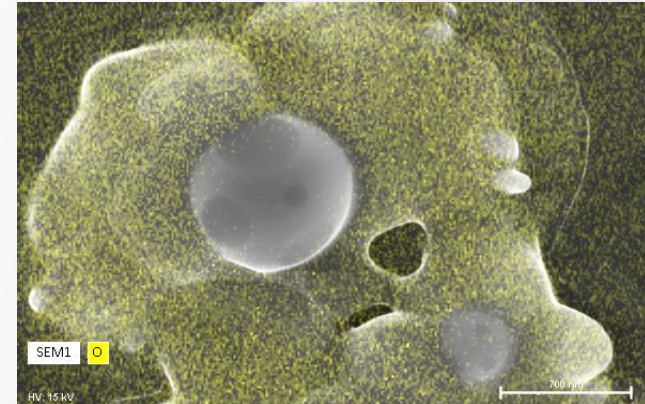


SE

Image courtesy: Min Wu, Thermo Fisher Brno



Iron (Fe)



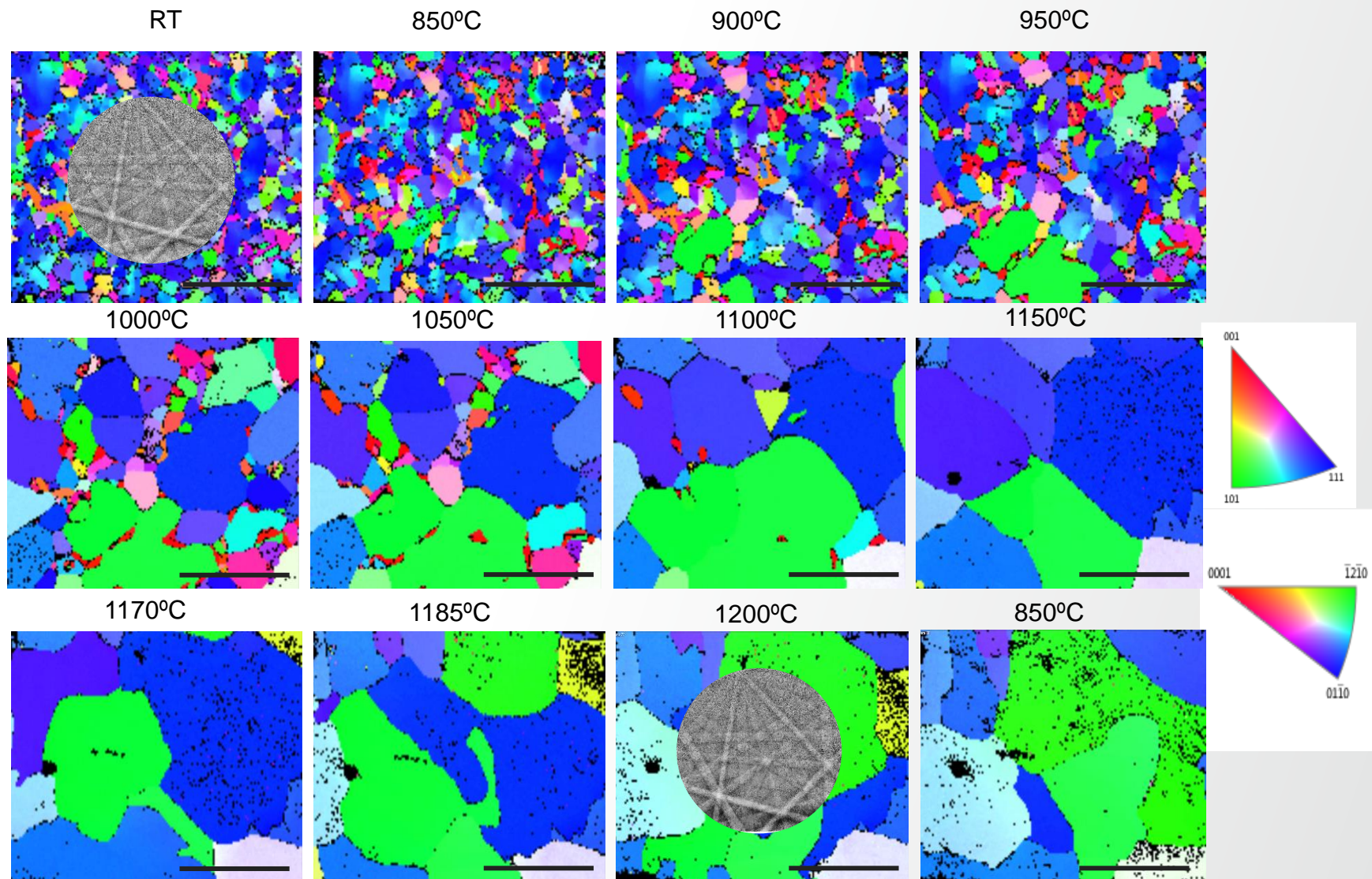
Oxygen (O)

- Magnetite-hematite shows elemental separation during melting
- Small footprint: no effects on imaging and detection
- EDS signal remains reliable even at high temperature



μHeater: high quality, high temperature analytics

μ Heater enables in situ EBSD at Elevated Temperature

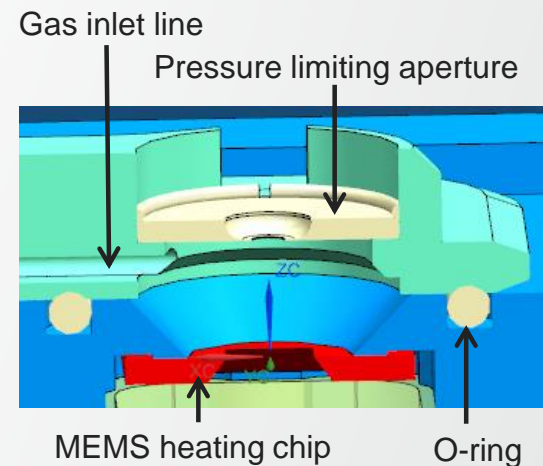
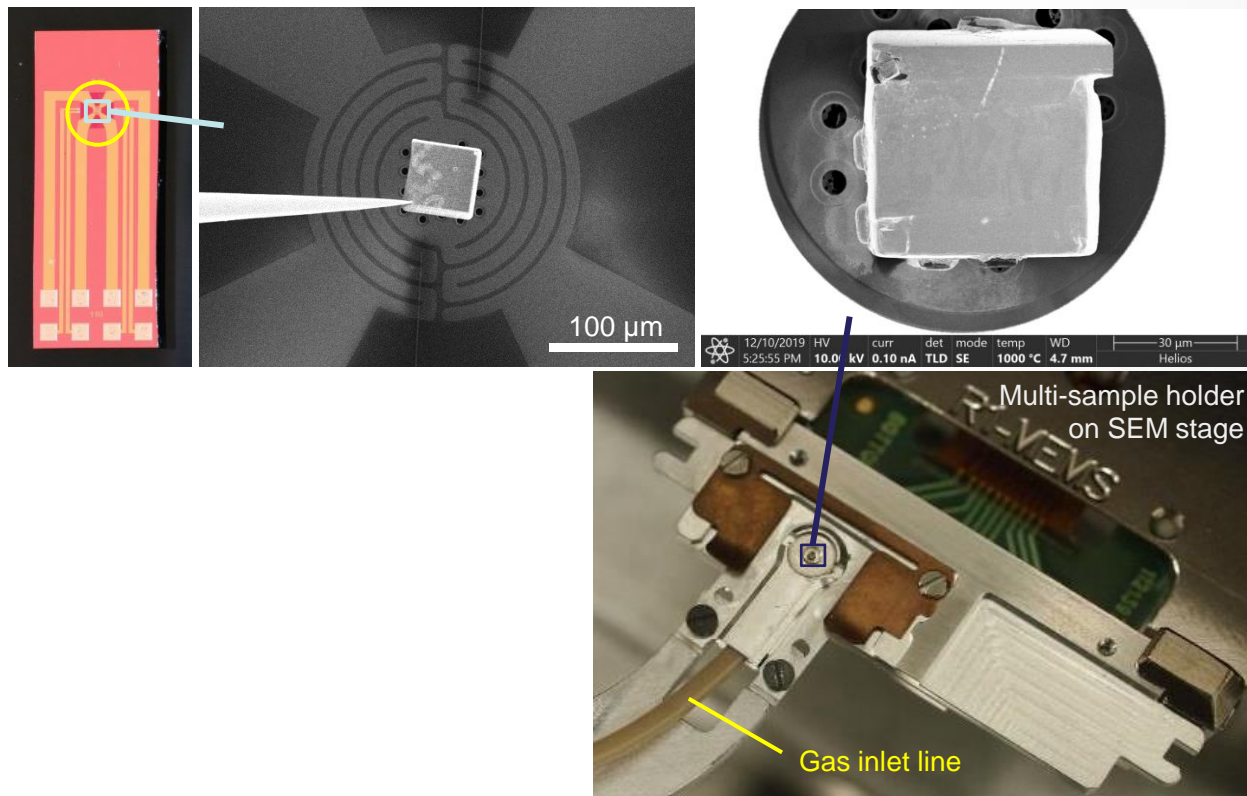


Sequential original IPFZ maps show a distinct recrystallization and grain growth (grain boundary migration) process at elevated temperatures. Each map was acquired at 20kV, 11nA, with a step size 0.3 μ m, in approximately 7 minutes. Scale bar in each map is 20 μ m.

Image courtesy: Min Wu, Thermo Fisher Brno

Ti-6Al-4V alloy

μ Reactor enable real time chemical reaction



Reactor volume: 7 μ l
Inlet flow rate: units of sccm
Max. pressure: 500 Pa
(<1E-2 Pa in SEM chamber)

Titanium oxidation growth

Ti substrate

Temperature 850°C

Acetone vapor (~ 100 Pa)

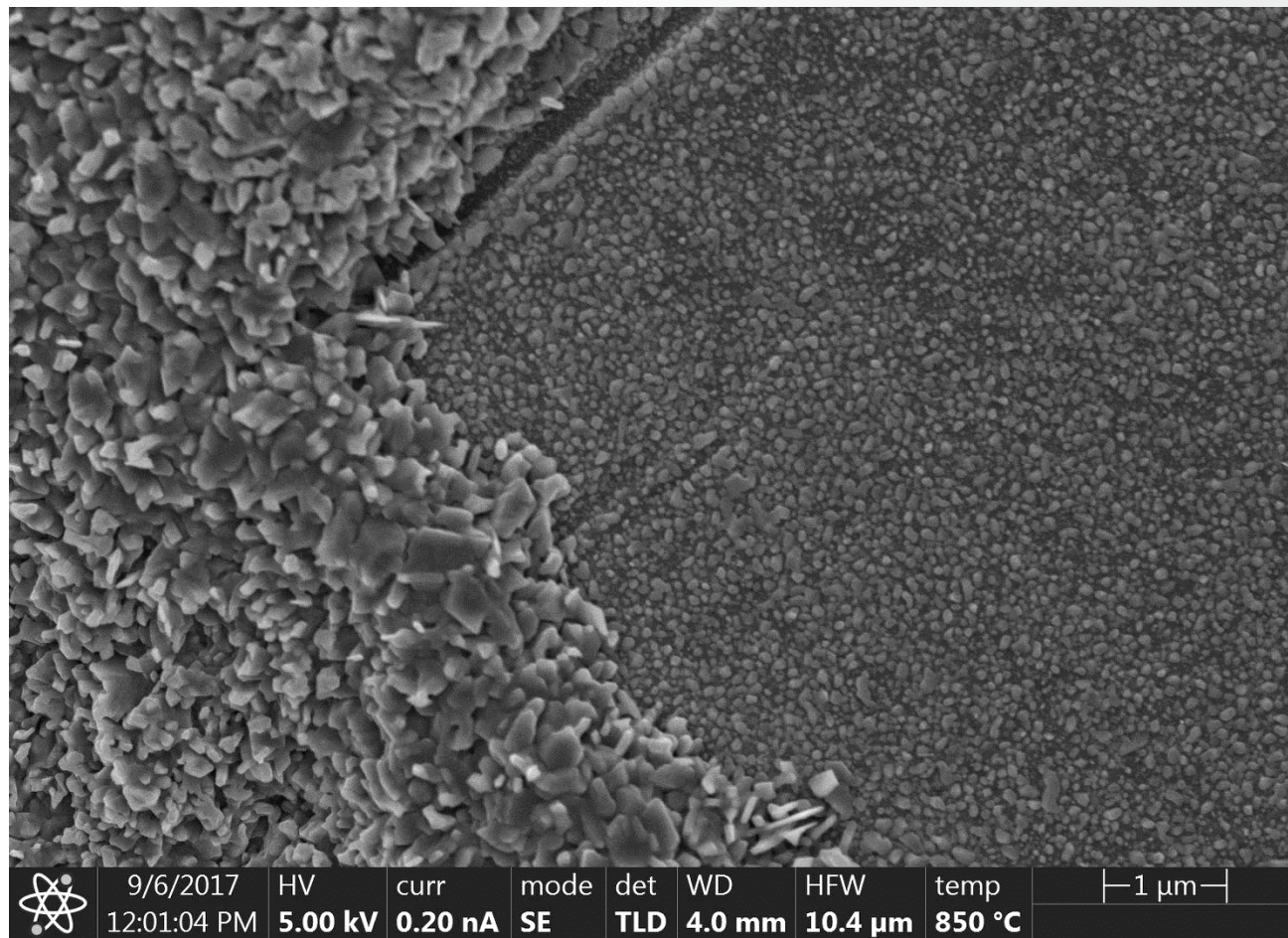
Formation of TiO_2 crystals

Imaging:

UHR mode of Helios

TLD-SE in-column detection

Acquisition as it is
(no registrations
no drift correction)



Tungsten oxide nanowires from WS₂

WS₂ sample oxidized in water vapor, forming tungsten oxide nanowires.

$t = 700^{\circ}\text{C}$, $p(\text{H}_2\text{O}) \sim 50 \text{ Pa}$
High resolution imaging in UHR mode in gas.

Formation of Tungsten Oxide Nanowires by Electron-Beam-Enhanced Oxidation of WS₂ Nanotubes and Platelets

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[‡]CEITEC BUT, Brno University of Technology, Purkyňova 123, 612 00 Brno, Czech Republic

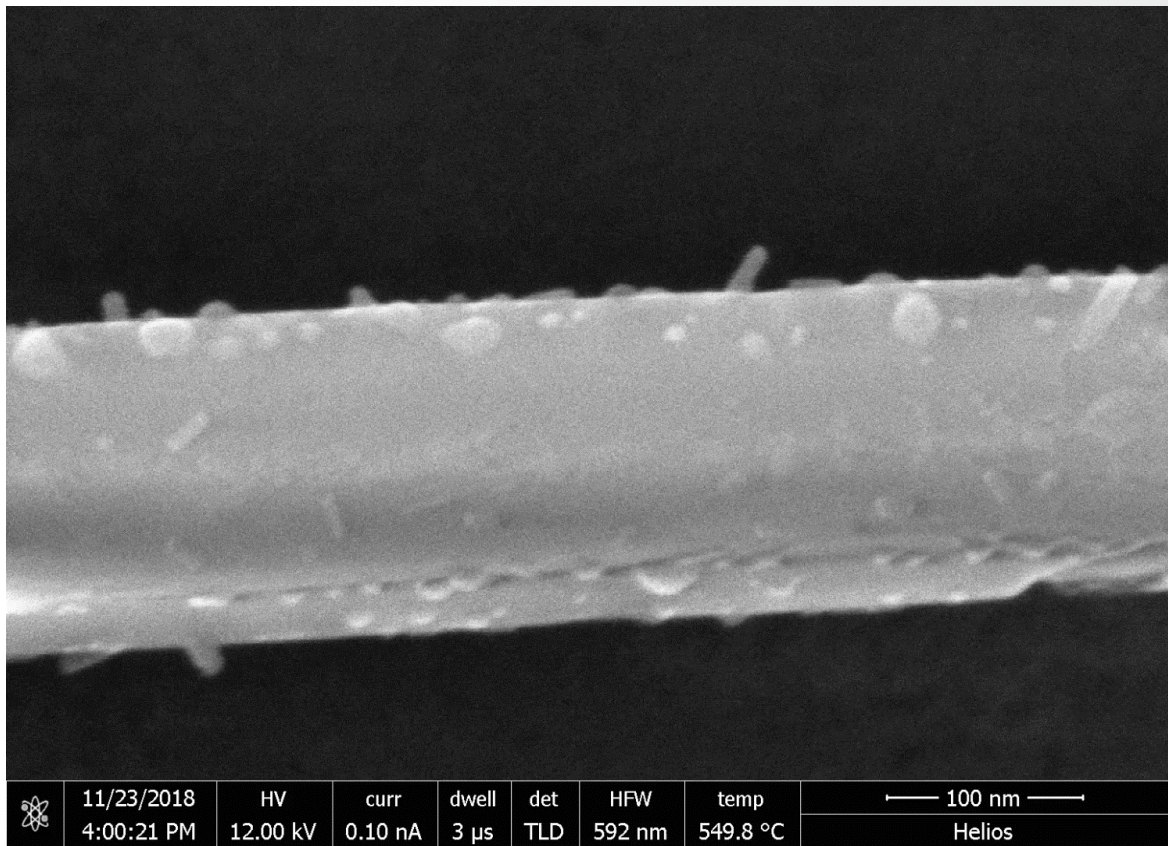
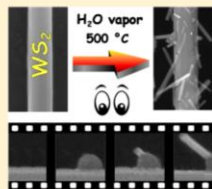
[§]Faculty of Sciences, Holon Institute of Technology, PO Box 305, IL-5810201 Holon, Israel

^{||}Department of Materials and Interfaces, Weizmann Institute of Science, Rehovot 76100, Israel

^{*}Thermo Fisher Scientific Brno, Vlastimila Pecha 12, 627 00 Brno, Czech Republic

Supporting Information

ABSTRACT: Oxidation of van der Waals-bonded layered semiconductors plays a key role in deterioration of their superior optical and electronic properties. The oxidation mechanism of these materials is, however, different from nonlayered semiconductors in many aspects. Here, we show a rather unusual oxidation of tungsten disulfide (WS₂) nanotubes and platelets in a high vacuum chamber at a presence of water vapor and at elevated temperatures. The process results in the formation of small tungsten oxide nanowires on the surface of WS₂. Utilizing real-time scanning electron microscopy, we are able to unravel the oxidation mechanism, which proceeds via reduction of initially formed WO₃ phase into W₁₈O₄₉ nanowires. Moreover, we show that the oxidation reaction can be localized and enhanced by an electron-beam irradiation, which allows for on-demand growth of tungsten oxide nanowires.



	11/23/2018 4:00:21 PM	HV 12.00 kV	curr 0.10 nA	dwell 3 μs	det TLD	HFW 592 nm	temp 549.8 °C	100 nm Helios
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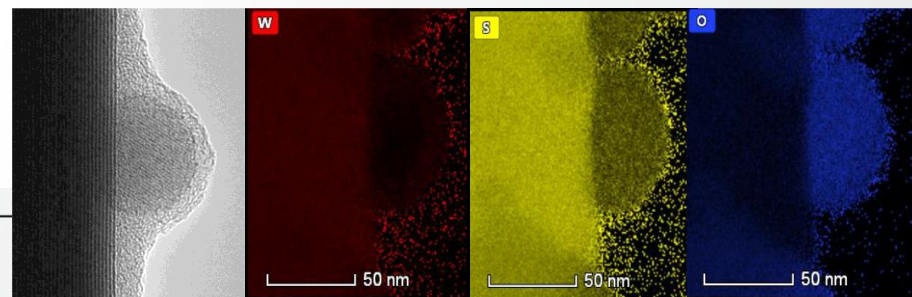
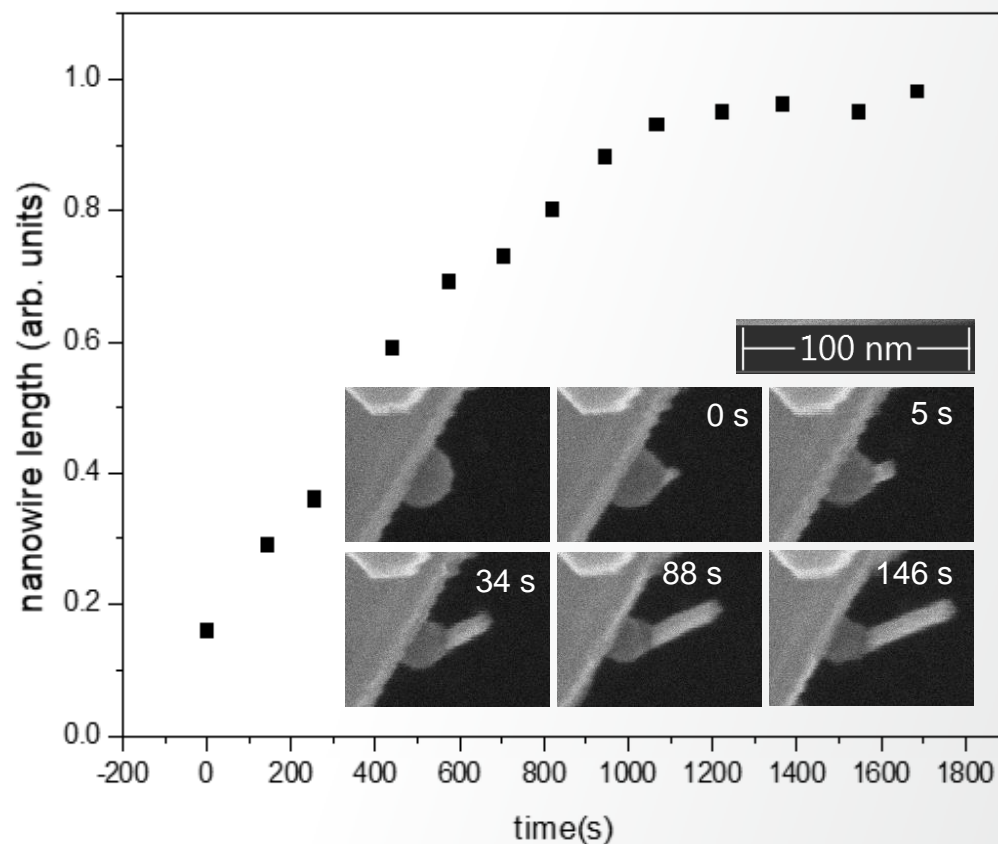
DOI: [10.1021/acs.jpcc.9b00592](https://doi.org/10.1021/acs.jpcc.9b00592)

Tungsten oxide nanowires from WS_2

MEMS chip compatible with TEM (NanoEx)

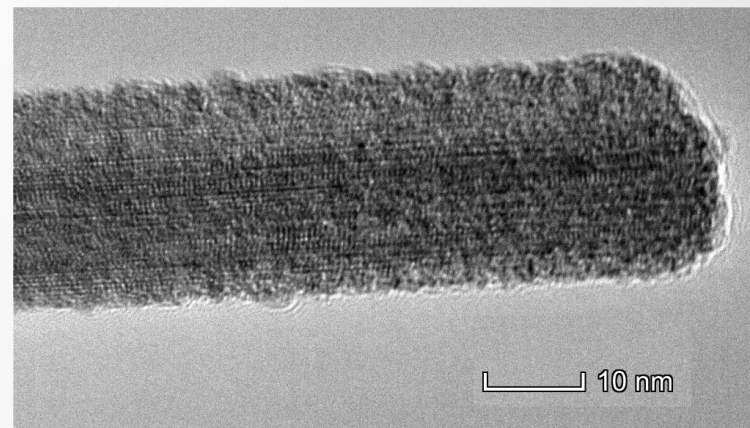
Start: sulfur oxide droplet

Growth kinetics from UHR SEM images:



W: 17.0 %
S: 0.0 %
O: 82.6 %

Tungsten oxide wire

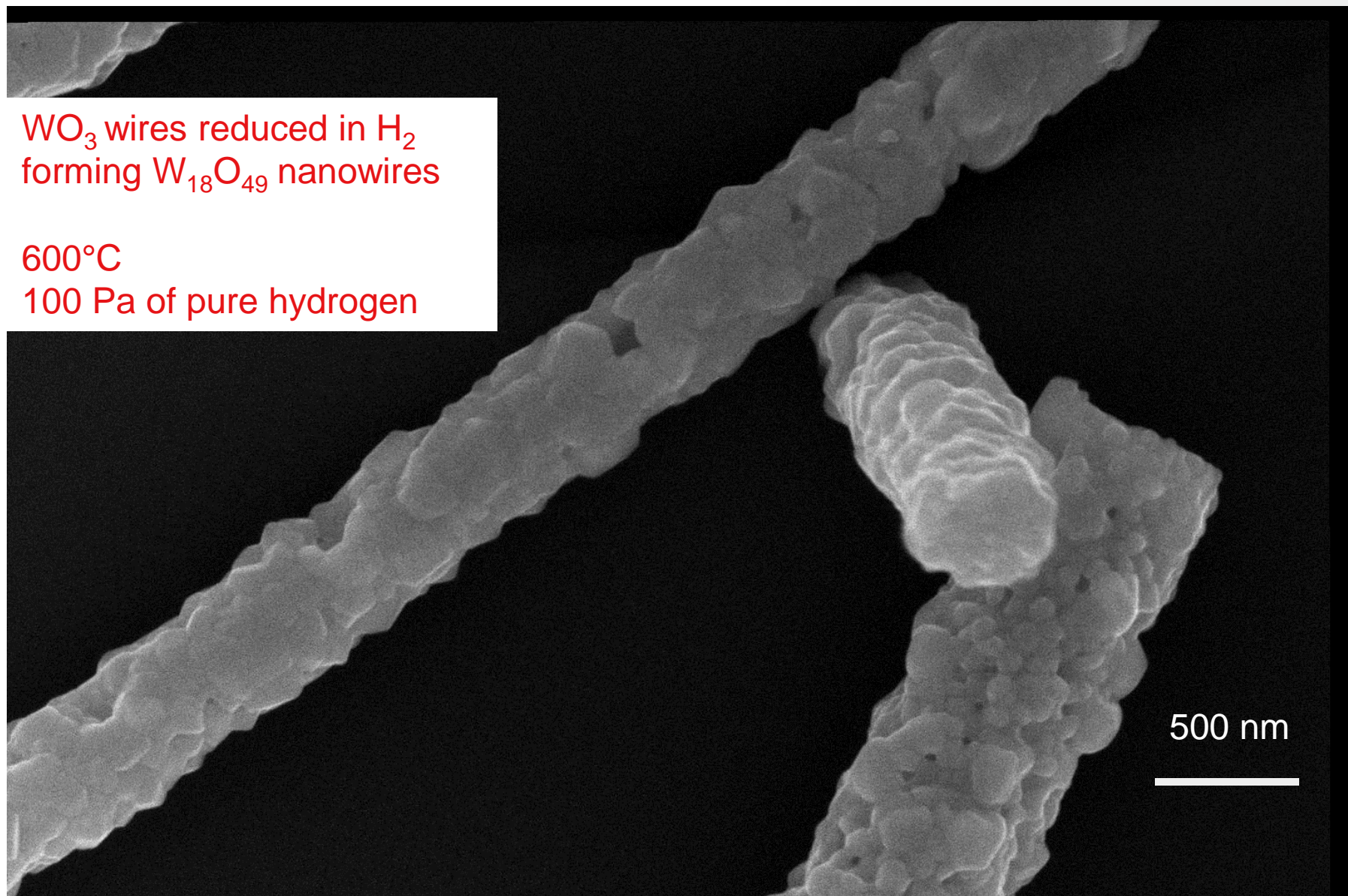


Tungsten oxide nanowires - reduction

WO_3 wires reduced in H_2
forming $\text{W}_{18}\text{O}_{49}$ nanowires

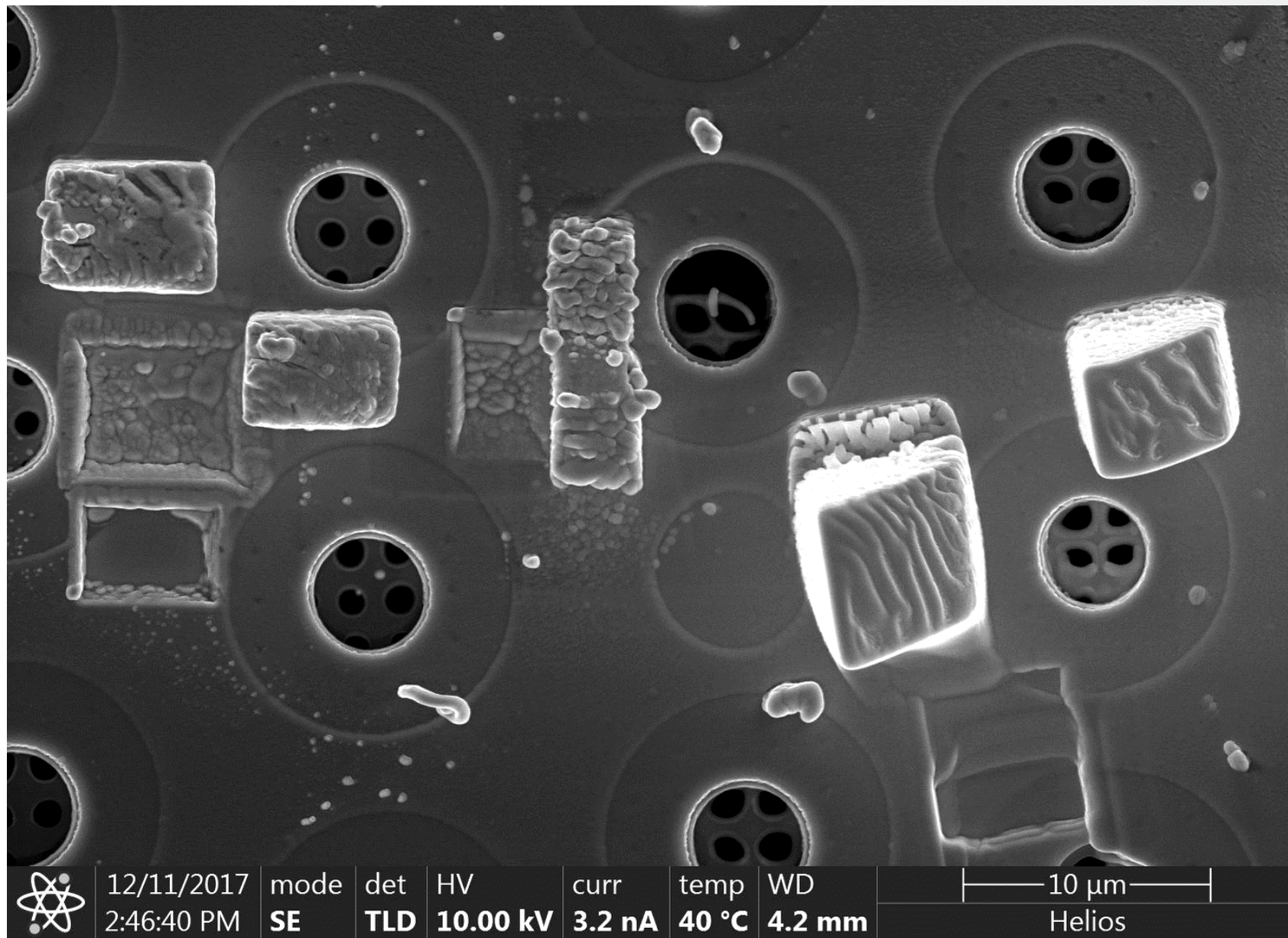
600°C

100 Pa of pure hydrogen



500 nm

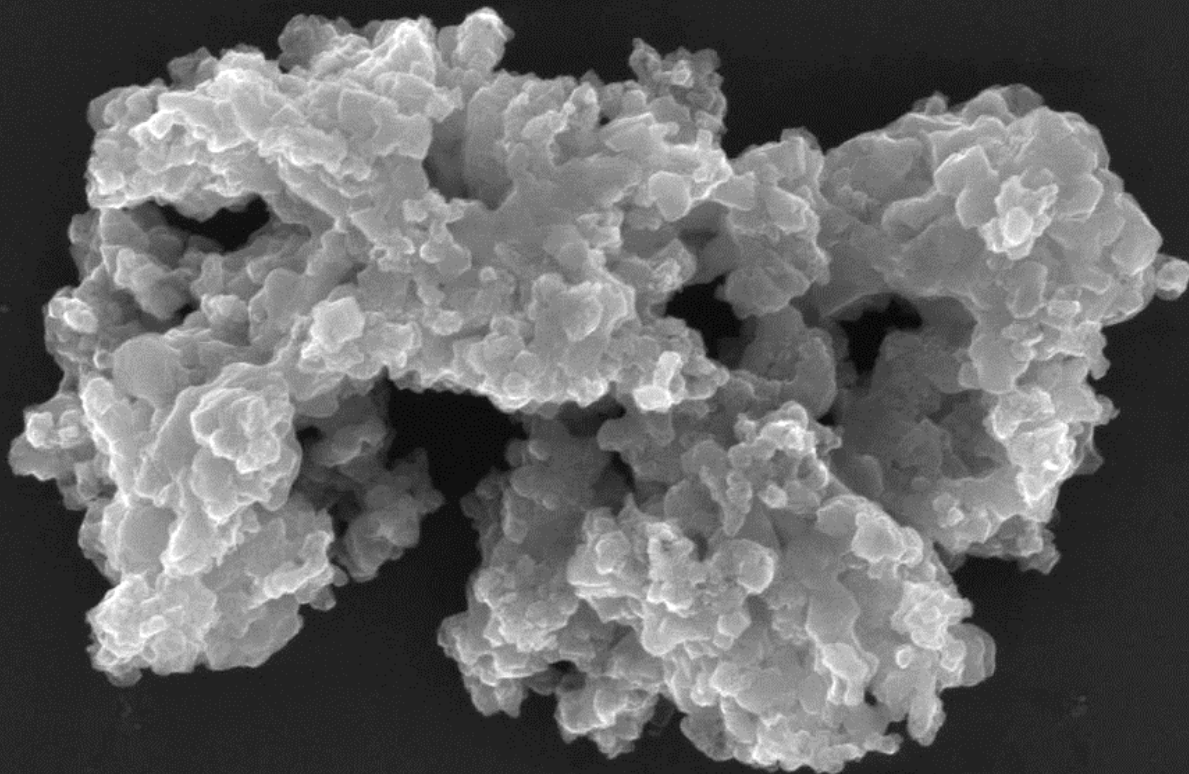
Pt-Ga wires growing in hydrogen



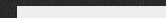
Iron carbide formation

Iron particle carburized
in methane

100 Pa methane
700°C

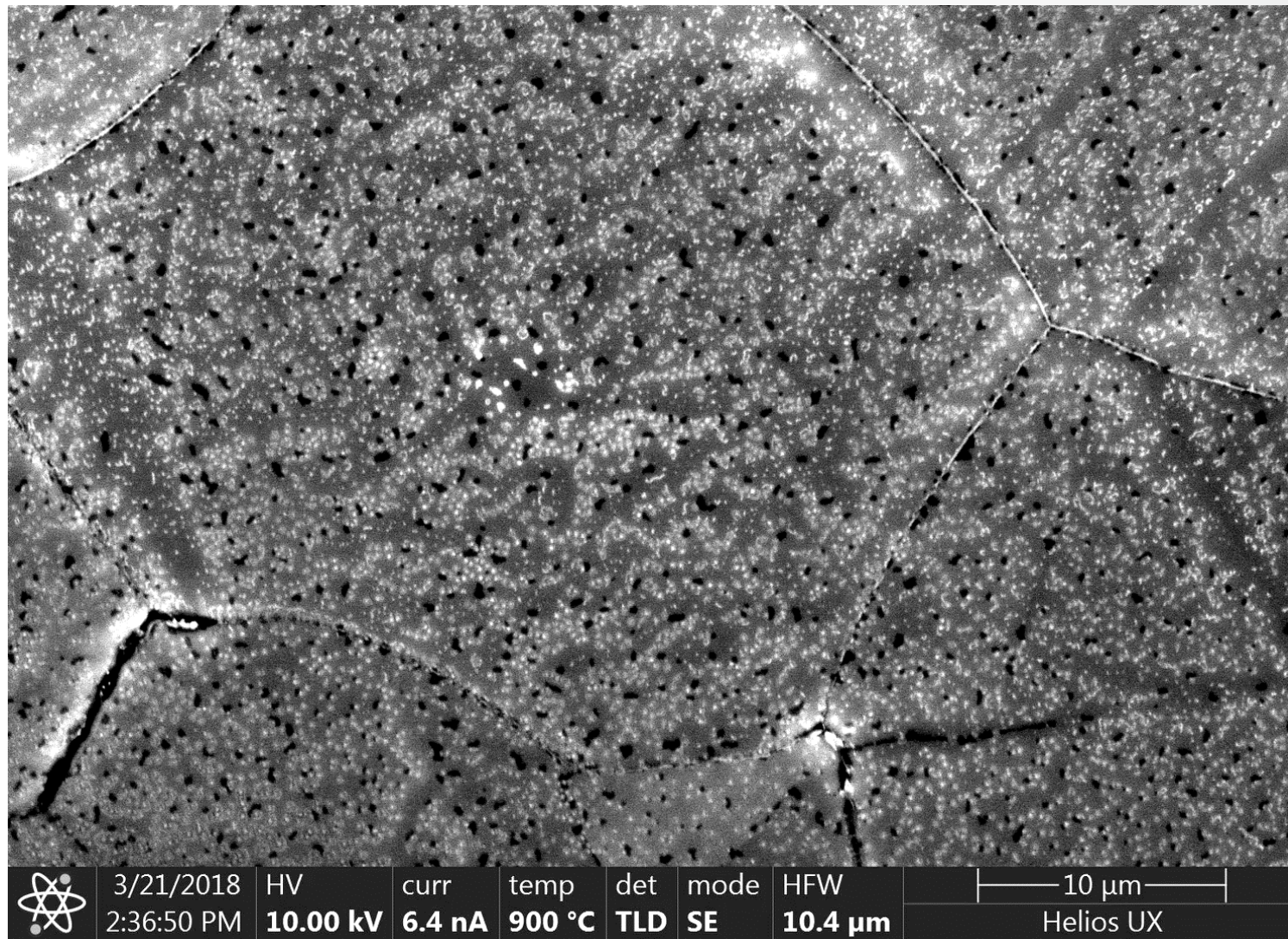


500 nm



Copper cleaning in hydrogen

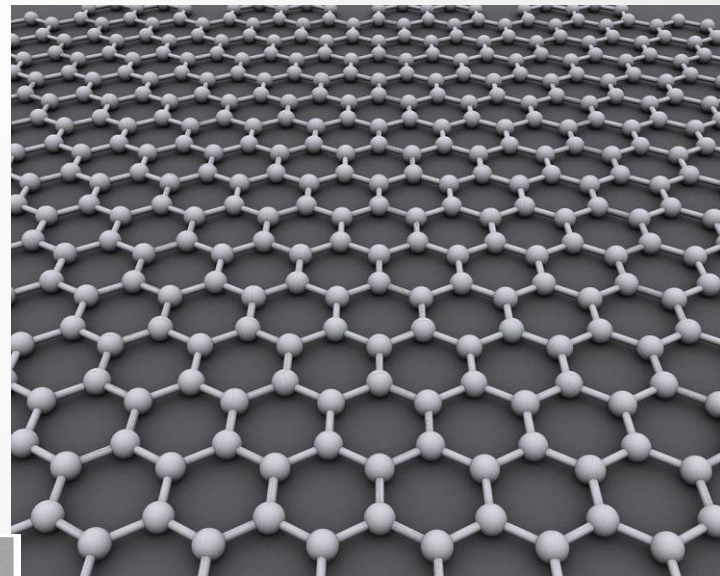
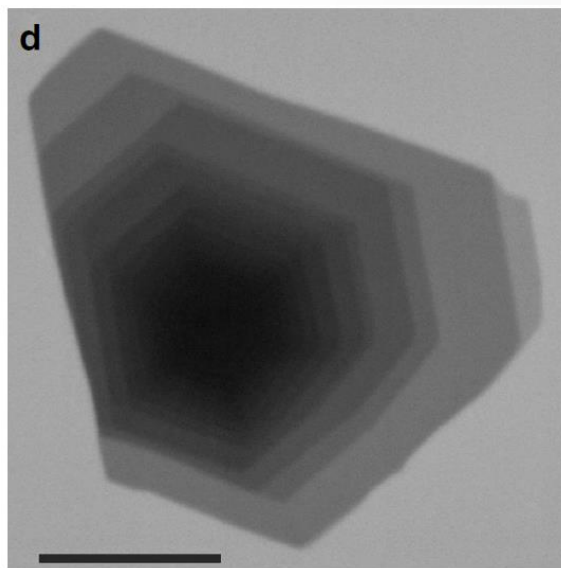
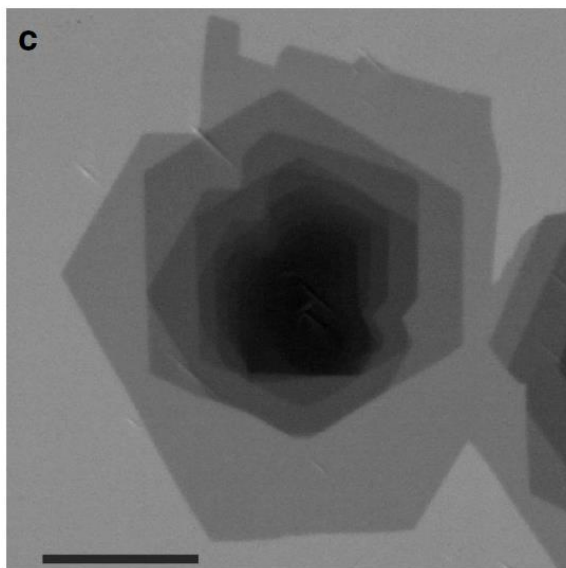
Polycrystalline copper (oxidized surface); Reduction in pure H₂ (50 Pa) at 1000°C.



Chemical vapor deposition: graphene

One of production methods of graphene is the CVD, which can be maintained in the μ Reactor and *in situ* imaged by SEM.

Graphene layers visible in signal of secondary electrons



Growth Dynamics, Stacking Sequence and Interlayer Coupling in Few-Layer Graphene Revealed by *in Situ* SEM

[Zhu-Jun Wang](#) et al., 2017

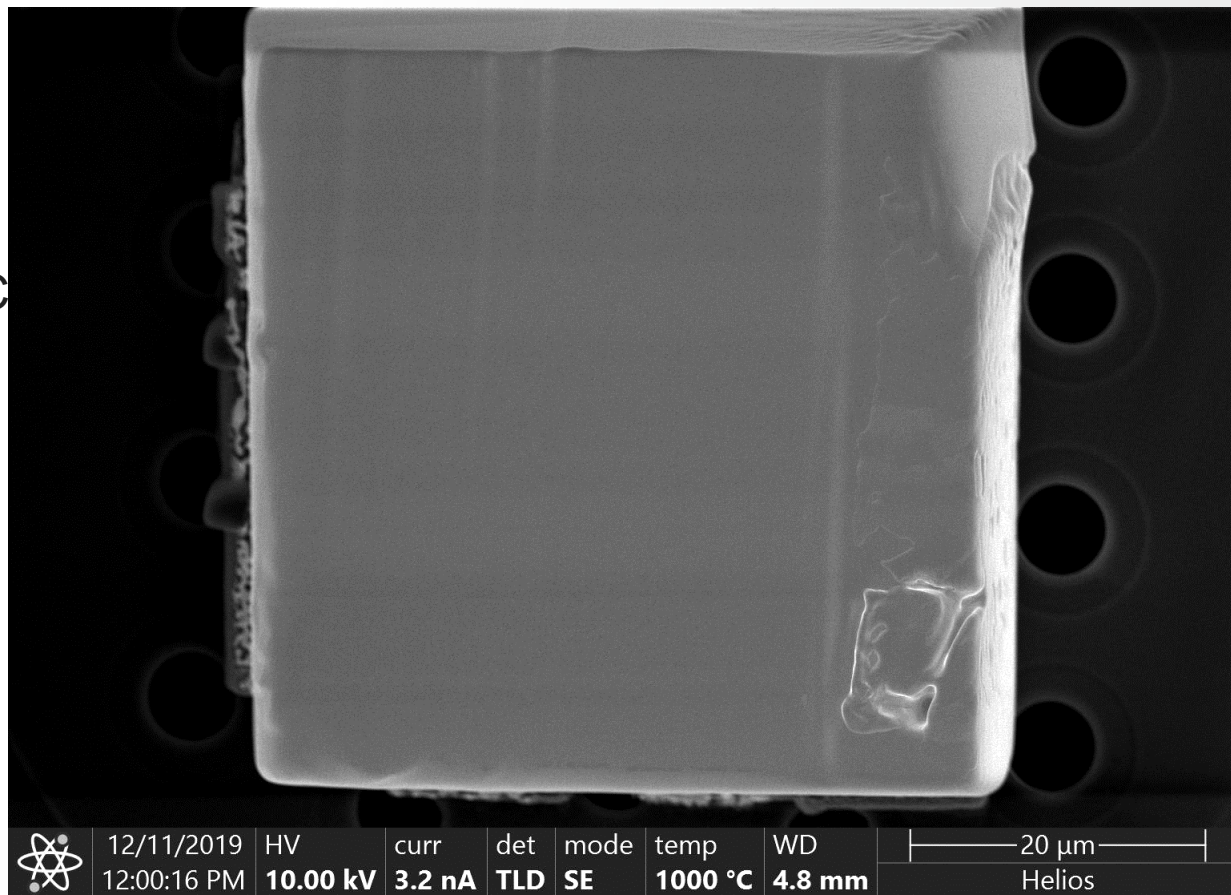
Microscopy and Microanalysis 23(S1):1746-1747

Chemical vapor deposition: graphene

Pt sample was first cleaned
in hydrogen at 1000°C
(H₂ pressure 30 Pa).

Ethylene introduced at 1000°C
(C₂H₄ pressure ~ 5 Pa)
to grow graphene monolayer.

Graphene monolayer grows
on polycrystalline Pt.



Publications with μ Reactor

M&M 2018

Control and in-situ imaging of heat & gas mediated processes in FIB/SEM system. (2018)
Novak et al. *Microscopy and Microanalysis*, 24(S1), 808-9.

M&M 2020

Microreactor for Clean and Controlled In-situ SEM Imaging of CVD Processes (2020) Novak, L., Wandrol, P., & Vesseur, E. *Microscopy and Microanalysis*, 26(S2), 1144-5.

Collaboration with Ceitec & Brno University of Technology & Weizmann Institute

Formation of Tungsten Oxide Nanowires by Electron-Beam-Enhanced Oxidation of WS₂ Nanotubes and Platelets (2019) Kolibal et al, *Journal of Physical Chemistry C*, 123, 14, 9552–9

Summary

A scanning electron micrograph (SEM) showing a dense network of thin, elongated, and somewhat curved Pt-Ga wires. The wires are light gray against a darker background, with some showing a more complex, branched structure. The overall texture is fibrous and intricate.

μReactor enables:

In situ imaging of heat and gas stimulated processes

Processing of bulk samples: FIB extraction from bulk

Clean & controlled environment in reactor

High Vacuum operation of the SEM (local ESEM around sample)

Compatibility with high vacuum FIB-SEM systems

Minimized sample oxidation / contamination by residual gases

Temperature & pressure control by MEMS heating chip

UHR imaging, detection by in-column detectors

Movie:

Pt-Ga wires growing in hydrogen at 850°C

image width 9 μm